

# Pressure sensors

- definition:

$$p = \frac{dF}{dS}$$

F .. force [N]

S .. area [m<sup>2</sup>]

1 atm = 100 kPa

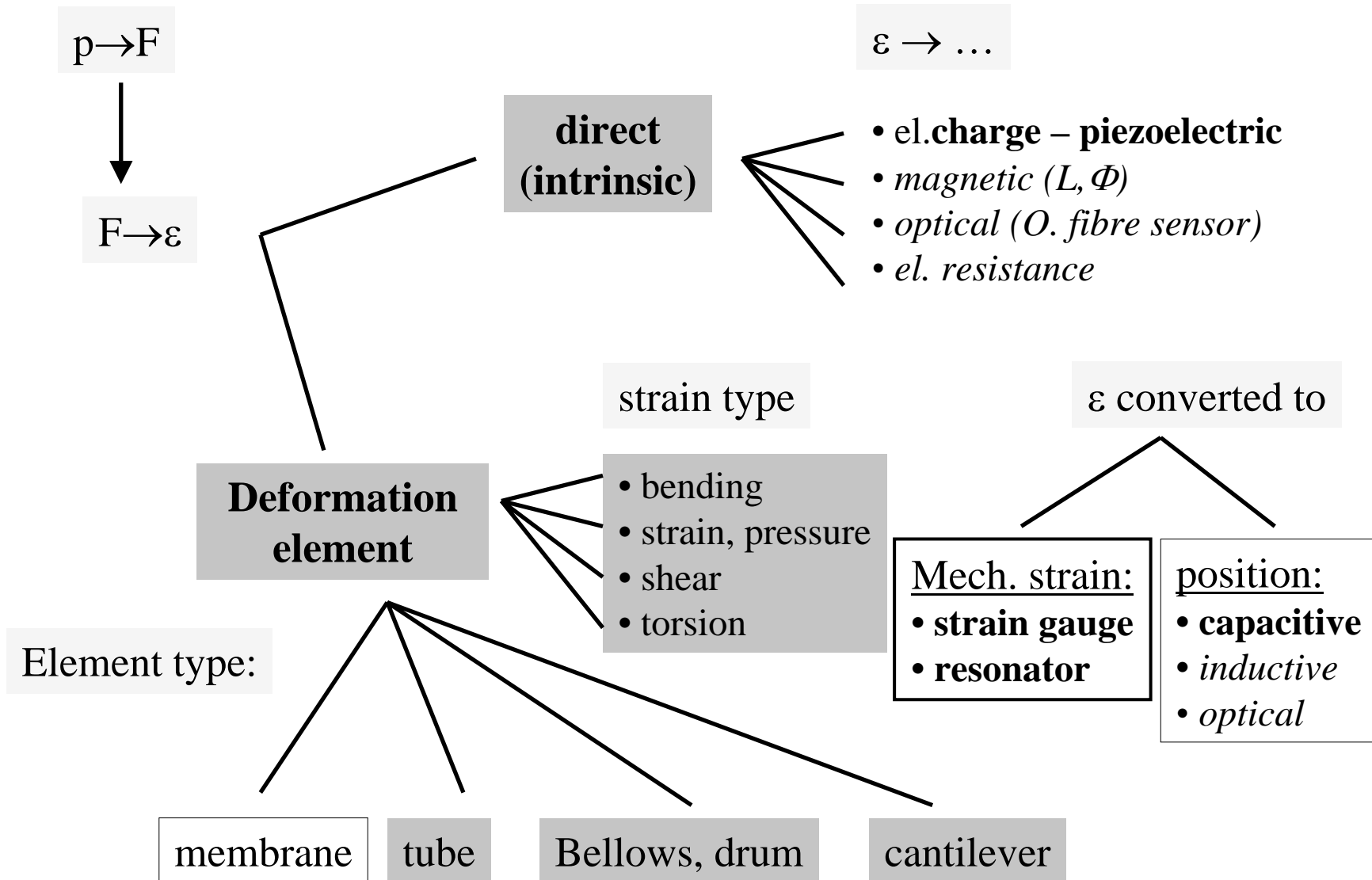
2 ways of measurement:

$p \rightarrow F \rightarrow \varepsilon$  deformation element  $\rightarrow$  change in dimensions

**direct (intrinsic) sensor**

**Strain gauge**

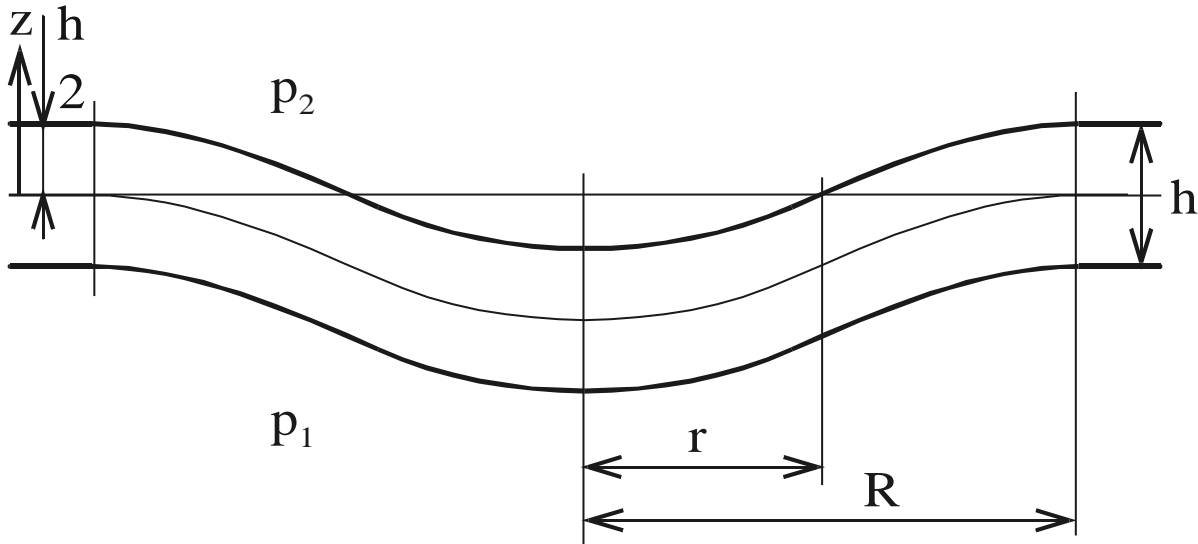
# Basic principles of pressure sensors



# 1. Membrane with strain gages

- most widely used

- membrane deformation:

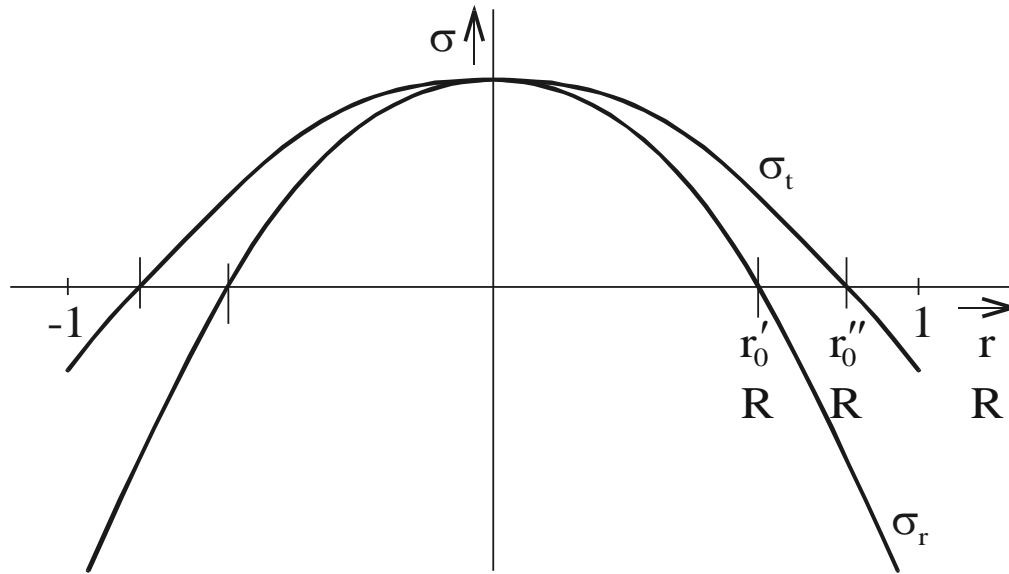


Action of pressure  $\Delta p = p_2 - p_1$  results in strain  $\sigma$  composed of:

$\sigma_r$  - radial component

$\sigma_t$  - tangential component

## Distribution of radial and tangential strain under pressure-deformation



$$\sigma_r = f_r(r/R)$$

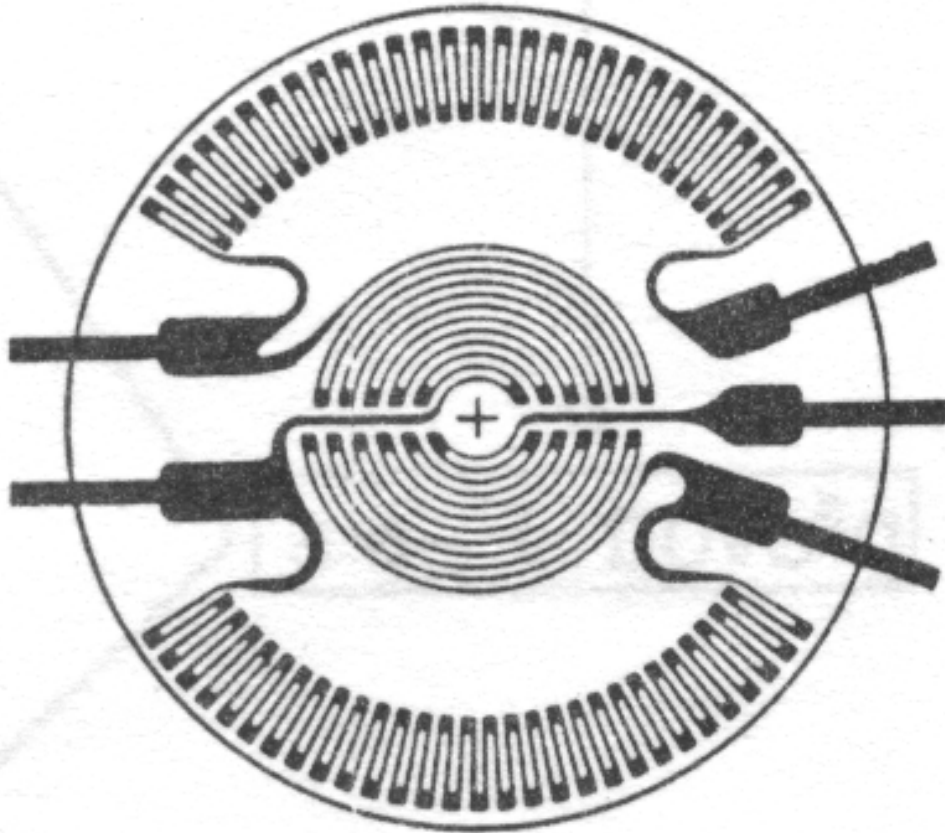
$$\sigma_t = f_t(r/R)$$

### **Metallic membrane:**

- glued semiconductive strain gauges
- metallic foil strain gauges
- thick layer deposition technology

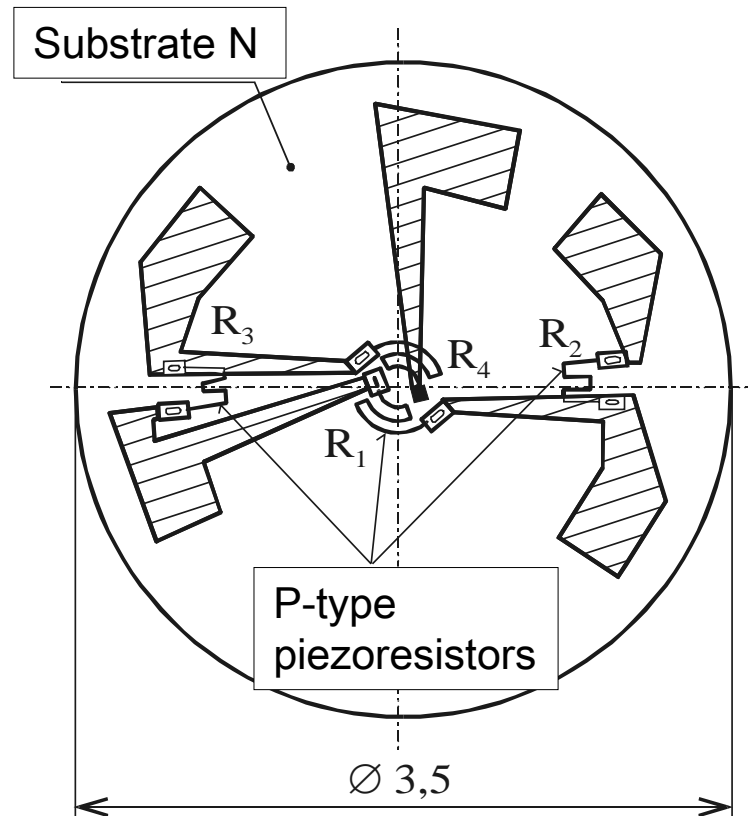
# Strain gauge „roseta“

- ideal strain gauge (-foil) for membranes
- 2 sensors at periphery and 2 in the middle



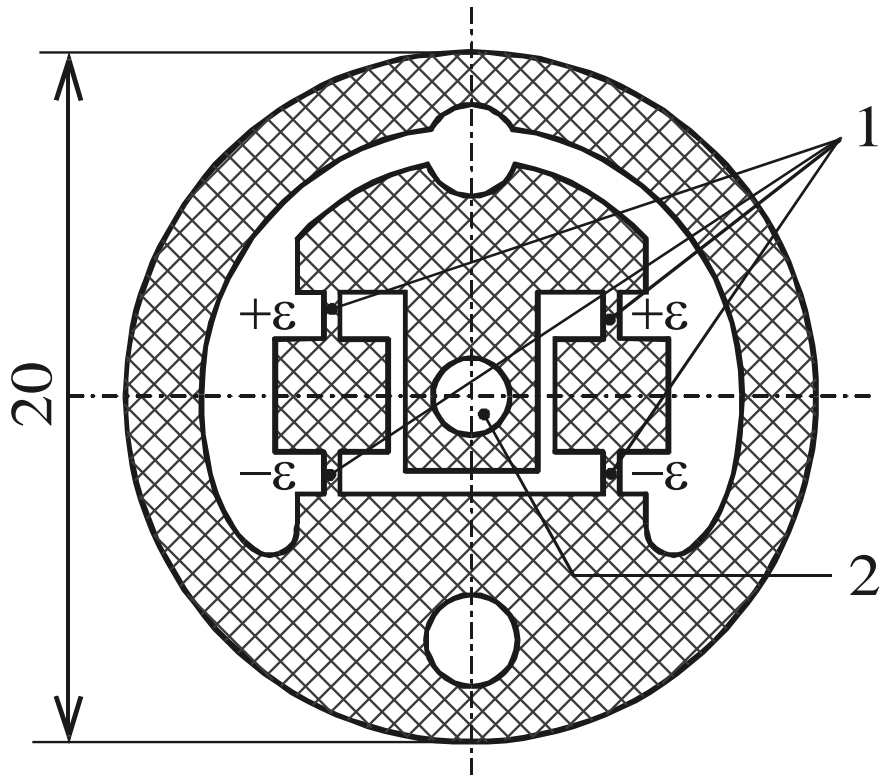
# semiconductive membrane

- + diffusion implemented piezoresistors
- made by integrated circuit technology  $\Rightarrow$  cheap
- Si, SiC, diamond



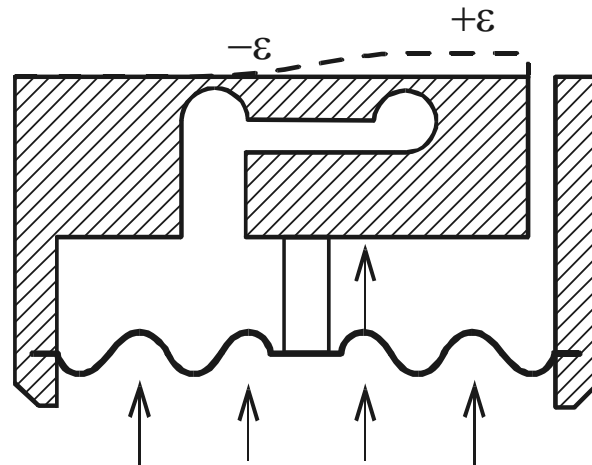
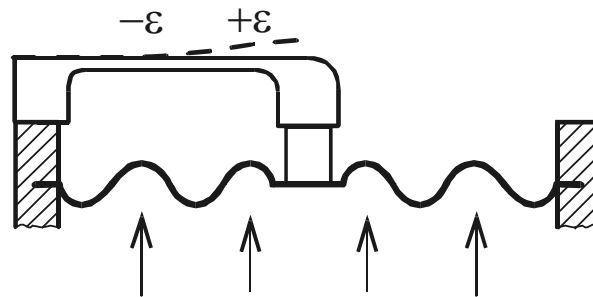
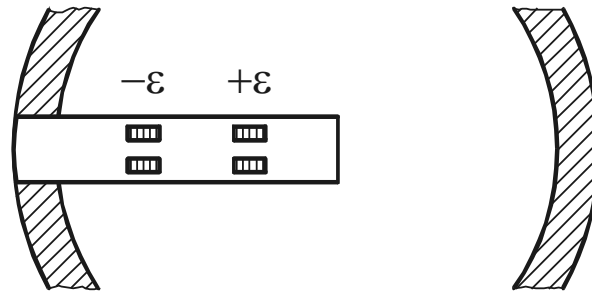
# Thin-layer pressure sensors

-Separation of measured environment from the sensor  $\Rightarrow$  use e.g. In measuring pressure in melting (transfer of deformation from outer durable membrane via connecting rod)



- 1 – four beams = deformation element
- 2 – connecting rod from outer membrane

# Deformation elements with cantilever and bellows

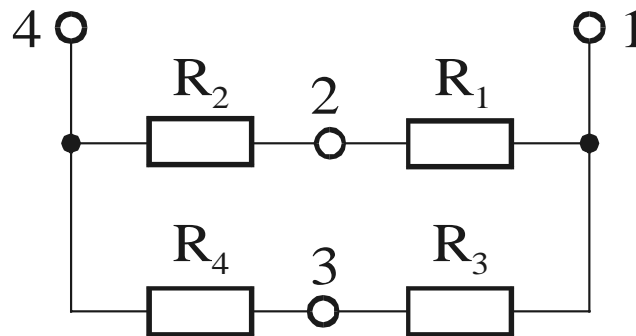
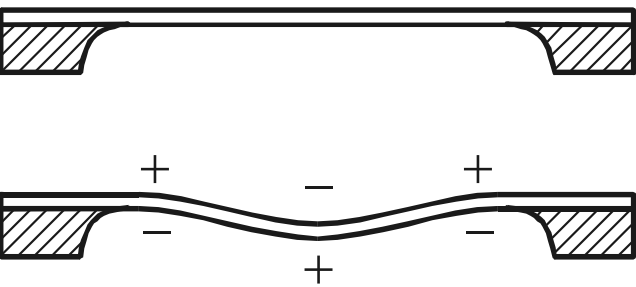
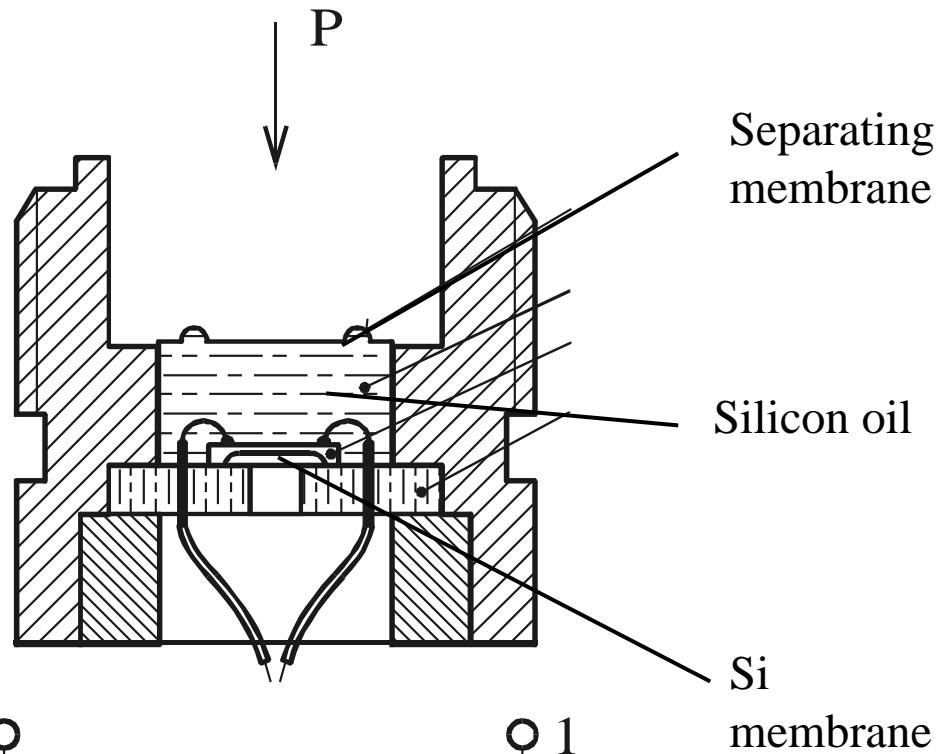
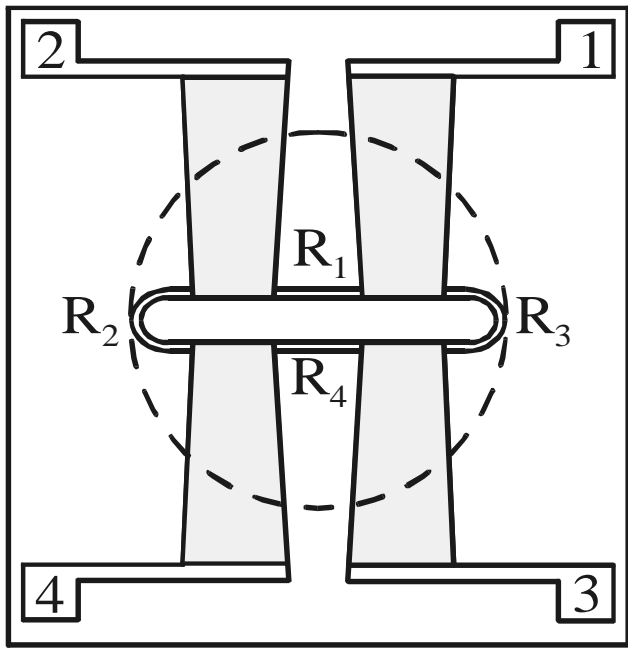




# Immersible pressure sensors

- Measuring of liquid level
- separation membrane, hermetic cable

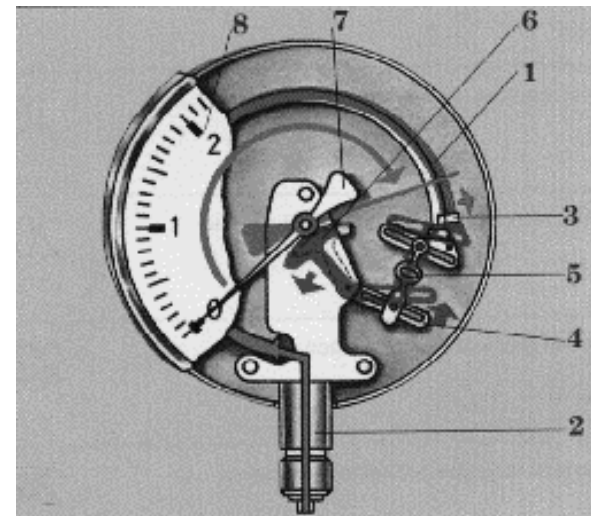
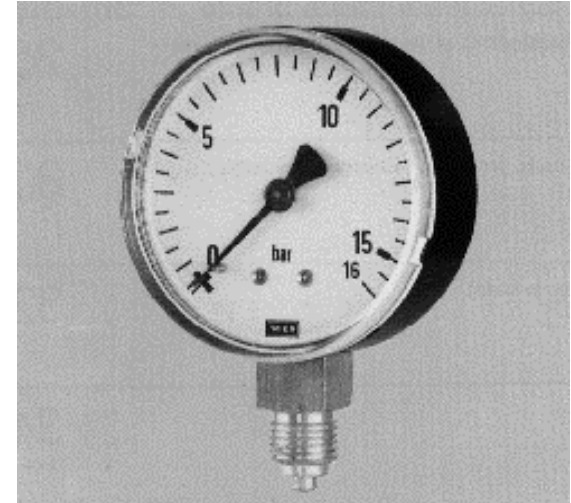
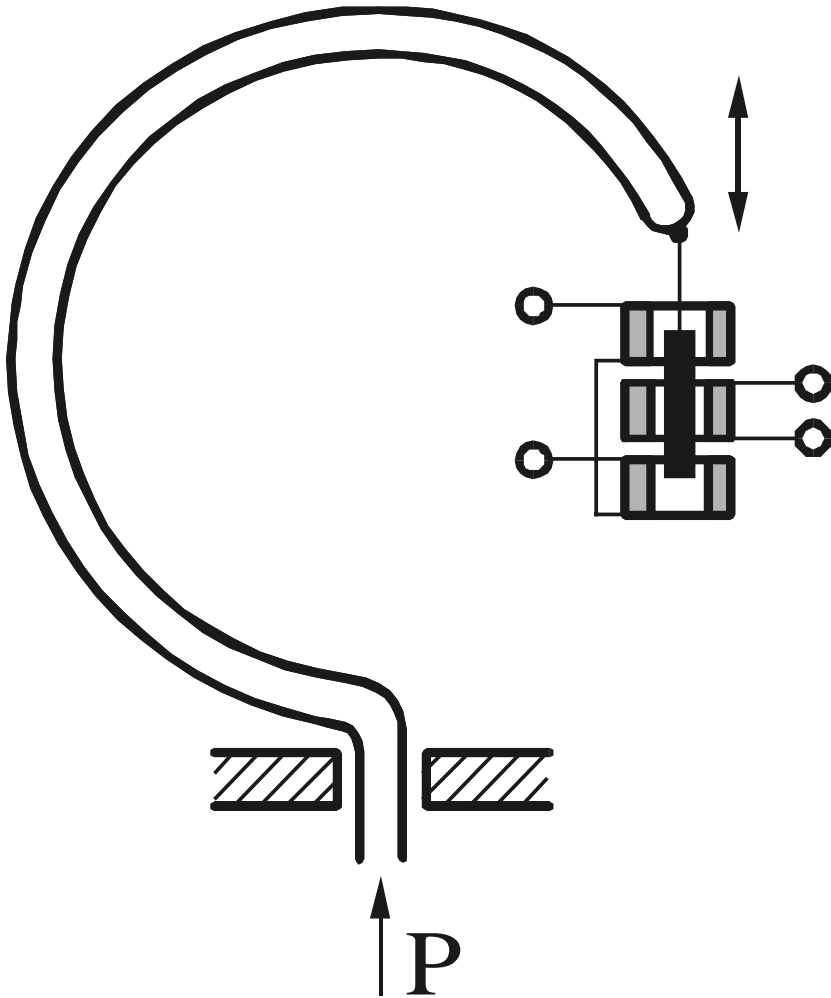




Membrane sensor with separating membrane

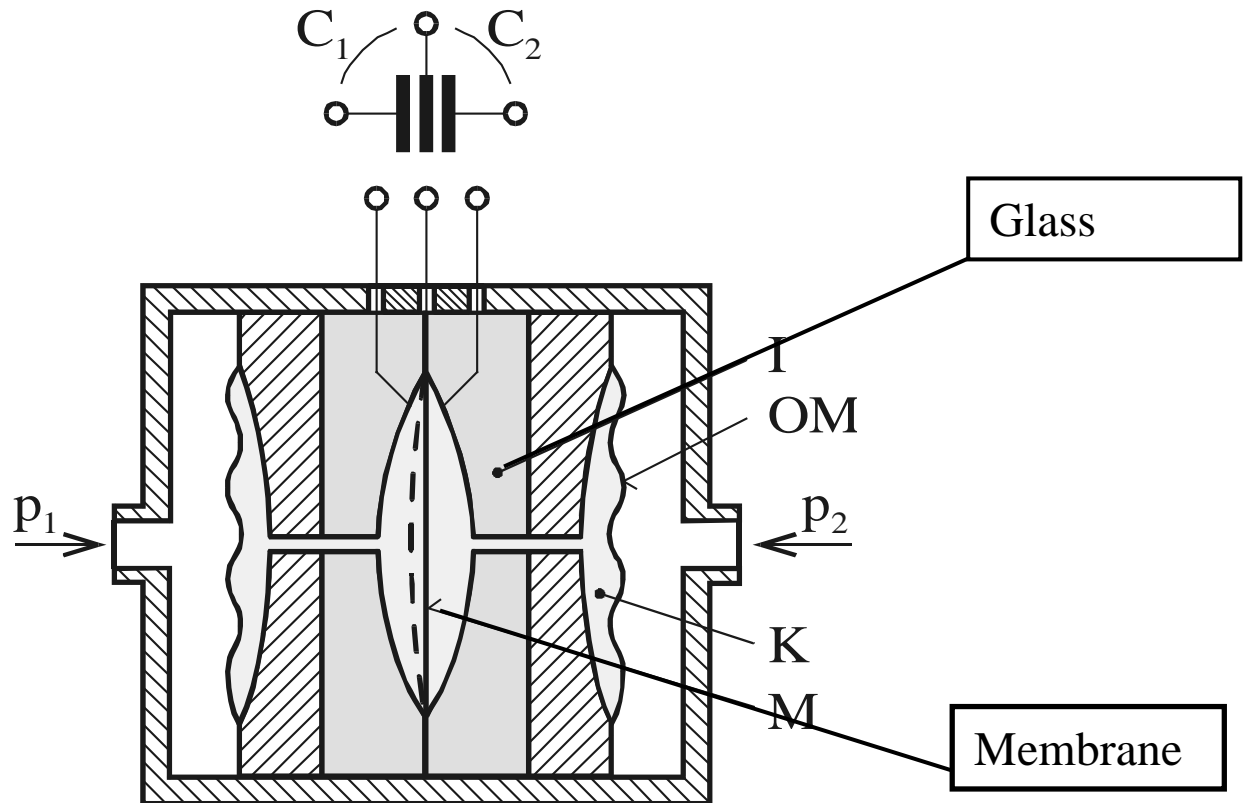
## 2. Deformation pressure sensors - tubes

Bourdon tube



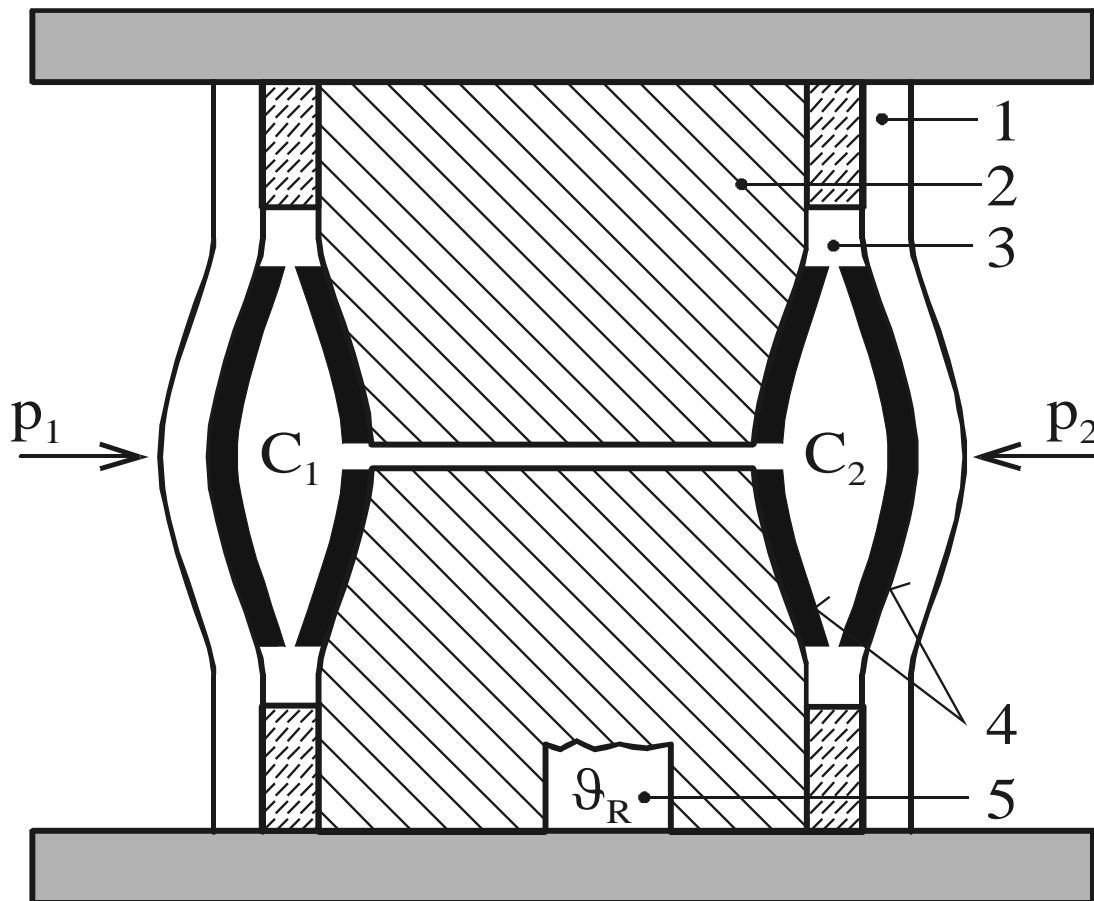
### 3. Capacitive pressure sensors

- capacitor – usually differential
- Deformation element = pre-strained metallic membrane – serves as grounded electrode
- Range:  $\Delta p = 1 \text{ mbar} - 10 \text{ bar}$ , total  $p$  up to 400 bar



Differential capacitor with separating liquid

# Pressure sensor with ceramic membranes

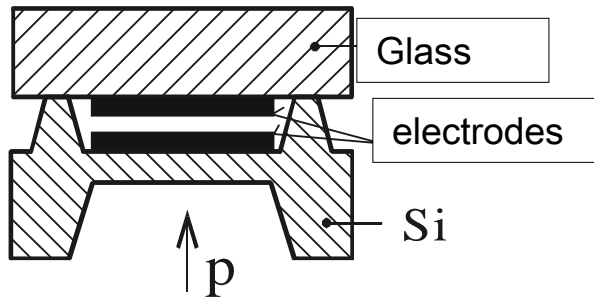


- 1- membrane
- 2 – central piece  $\text{Al}_2\text{O}_3$
- 3 - hydraulic liquid
- 4 - electrodes
- 5 - temperature sensor

0,1 %, max. 350°C

Range 2,5 to 300 kPa

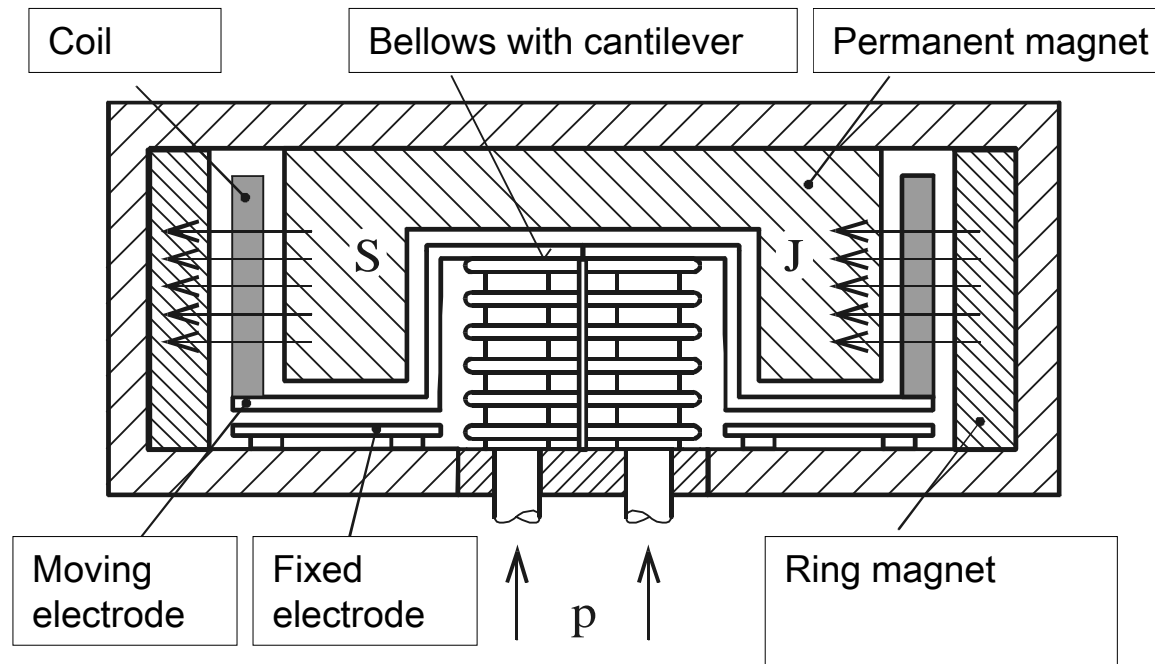
## MEMS sensor



- combination of Si membrane and capacitive sensor

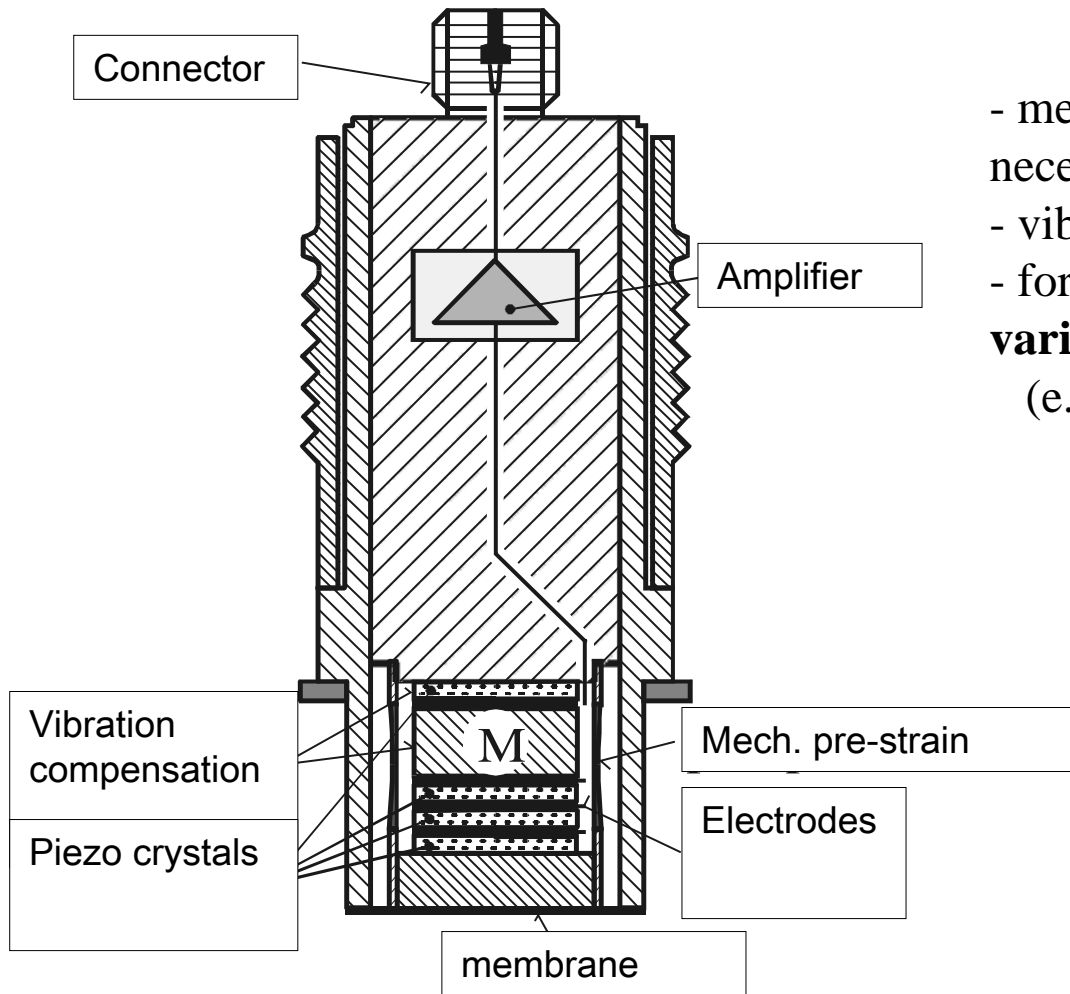
- returning membrane to idle position through electrostatic force
- range – up to 200 kPa

## Feedback sensor with bellows



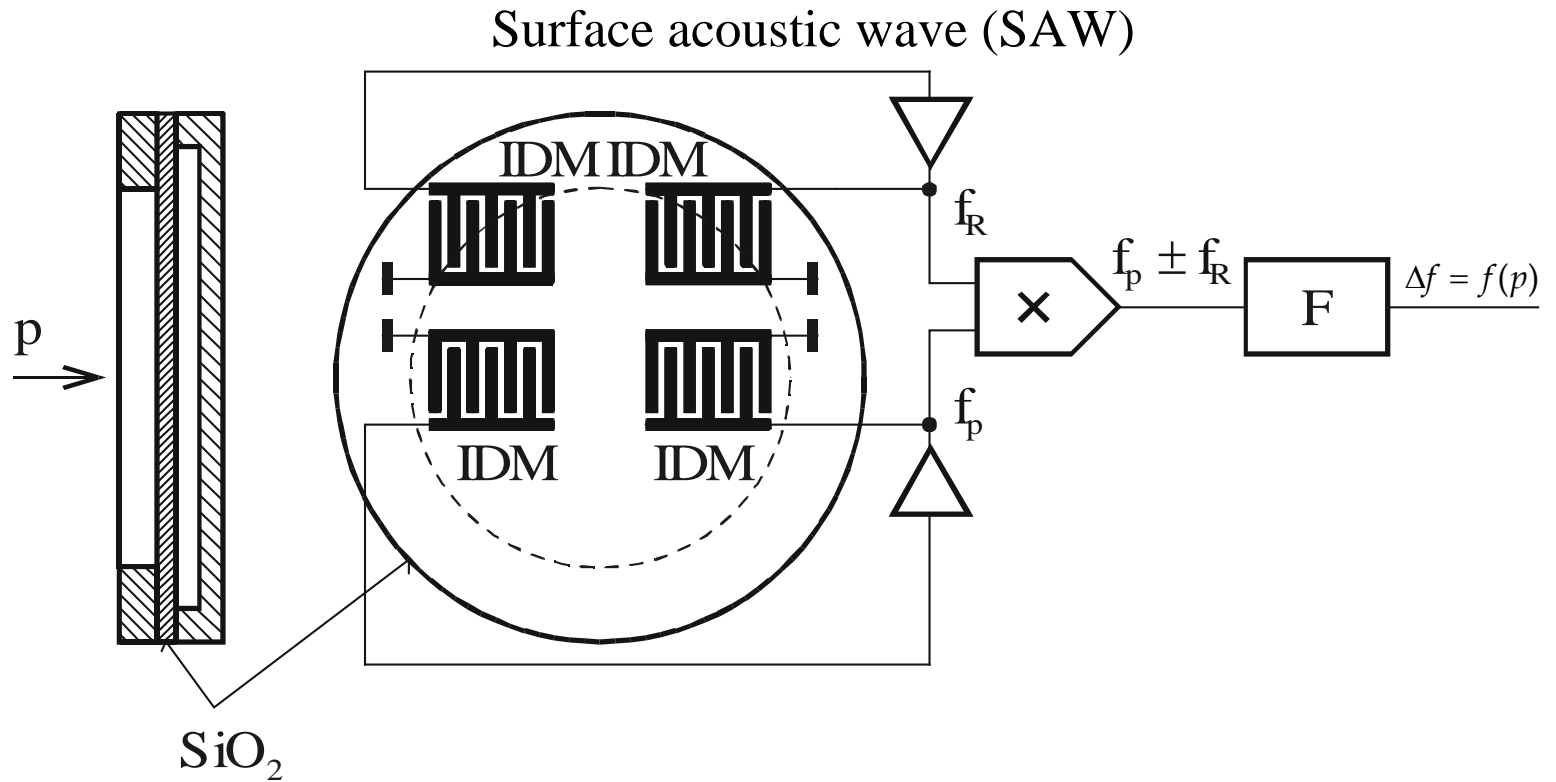
Very precise and expensive

## 4. Piezoelectric pressure sensor



- mechanical pre-strain of crystal is necessary
- vibration compensating necessary
- for measuring **fast pressure variations**  
(e.g. engine pistons)

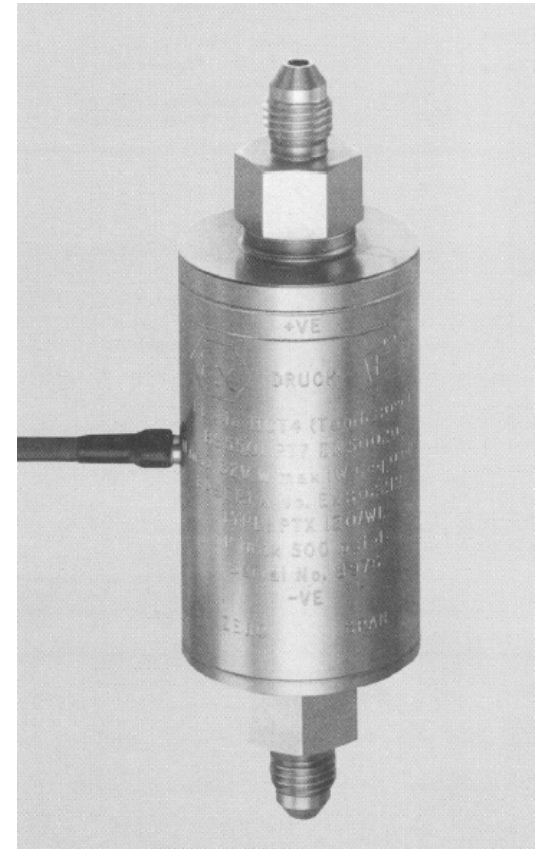
## 7. Resonant pressure sensors





# Examples of pressure sensors

- (separating metallic membrane) Si measuring membrane, piezoresistors, (integrated amplifier):  
PTX 120
- Process pressure sensor: HART or current loop: Capacitive  
STX 2100
- Resonant sensor „double fork“



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**STX 2100 Series**

Smart/HART® differential pressure transmitter



Ranges from 3.75 mbar to 20 bar

Accuracy  $\pm 0.1\%$ 

16:1 rangeability

Line pressures up to 140 bar

2-wire 4-20mA with HART® protocol

Robust and modular design

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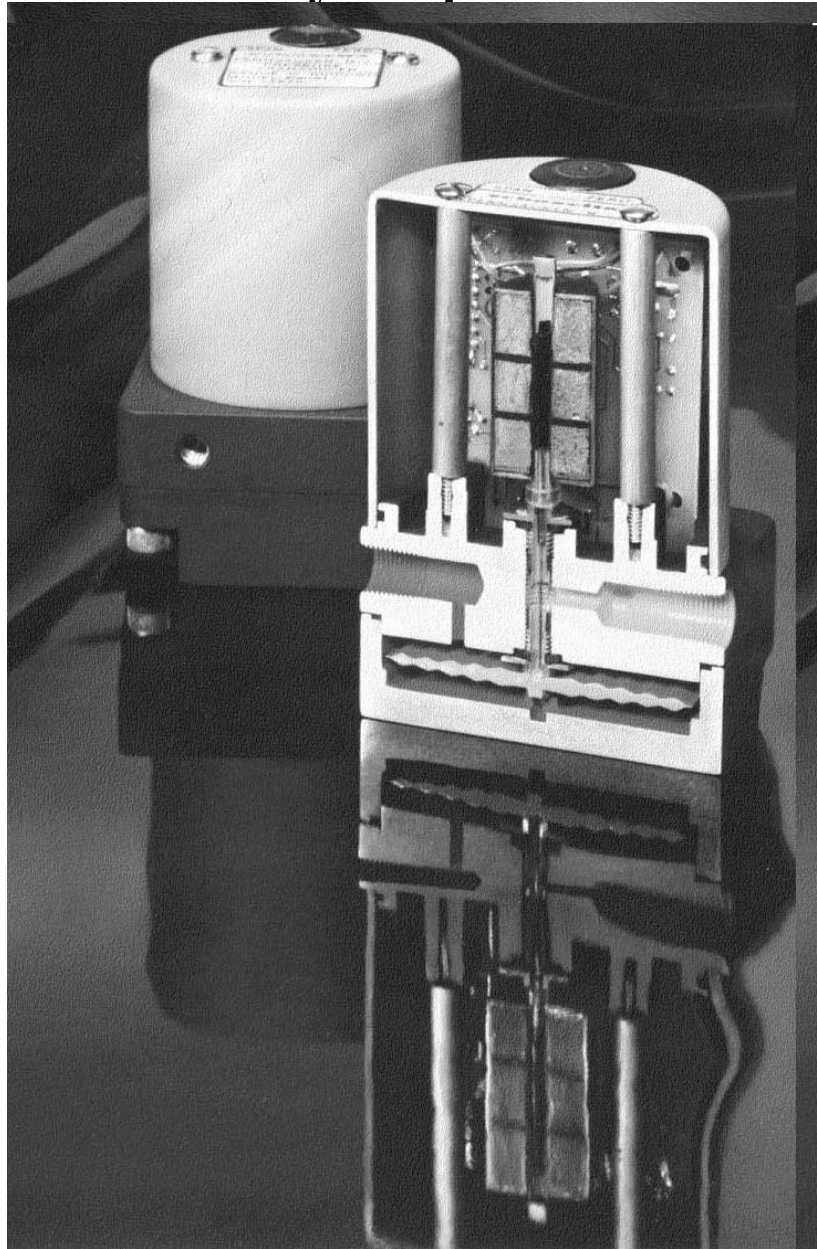
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At the heart of the instrument is a micro-capacitance silicon sensing element which floats remotely from the isolation diaphragm. Silicon has excellent mechanical properties, being perfectly free from hysteresis, and enables repeatability of better than 0.01% achieved.

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# Very low pressures

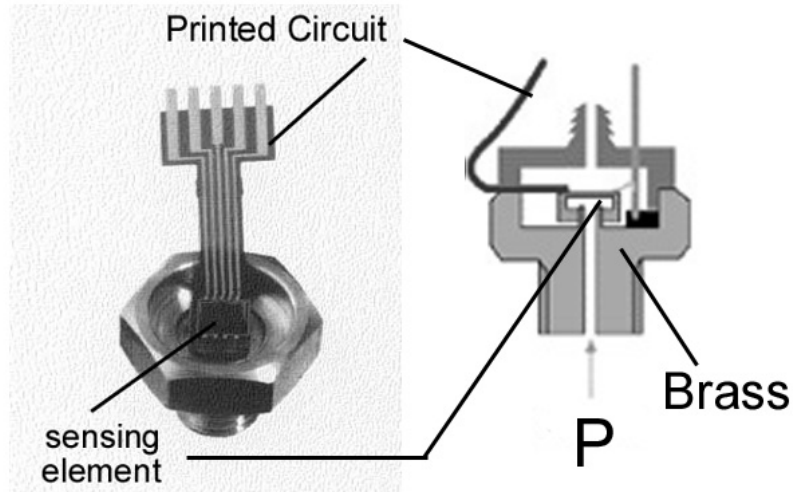
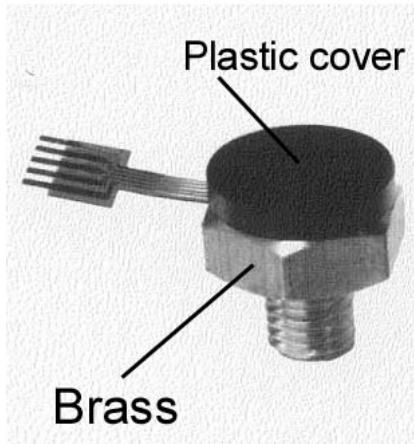
Principle: LVDT



SCHAEVITZ

# Piezoresistive pressure sensors

KELLER



## **SPECIFICATIONS (at 4 mA excitation)**

Pressure Ranges (FS)

Linearity

Stability

Operating Temperature Range

Storage Temperature

Temperature-Coefficients of...

- Zero (without Comp.)

- Sensitivity

1-20 bar

0,25% FS typ.      1% FS max.

0,5 mV typ.      2 mV max.

-10...80°C (optionally)

-20...100°C

0,05 mV/K typ.      0,2 mV/K max.

0,01%/K typ.      0,02%/K max.

# Integrated pressure sensors

- Pure CMOS based sensor
- calibrated to automotive specifications

